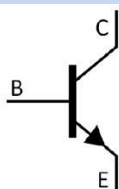


TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

V_{CEO} , KSA708

High V_{CEO} , Complementary pair with KSA708.

Low frequency amplifier, medium speed switching.



PIN1 Collector PIN 2 Base PIN 3 Emitter

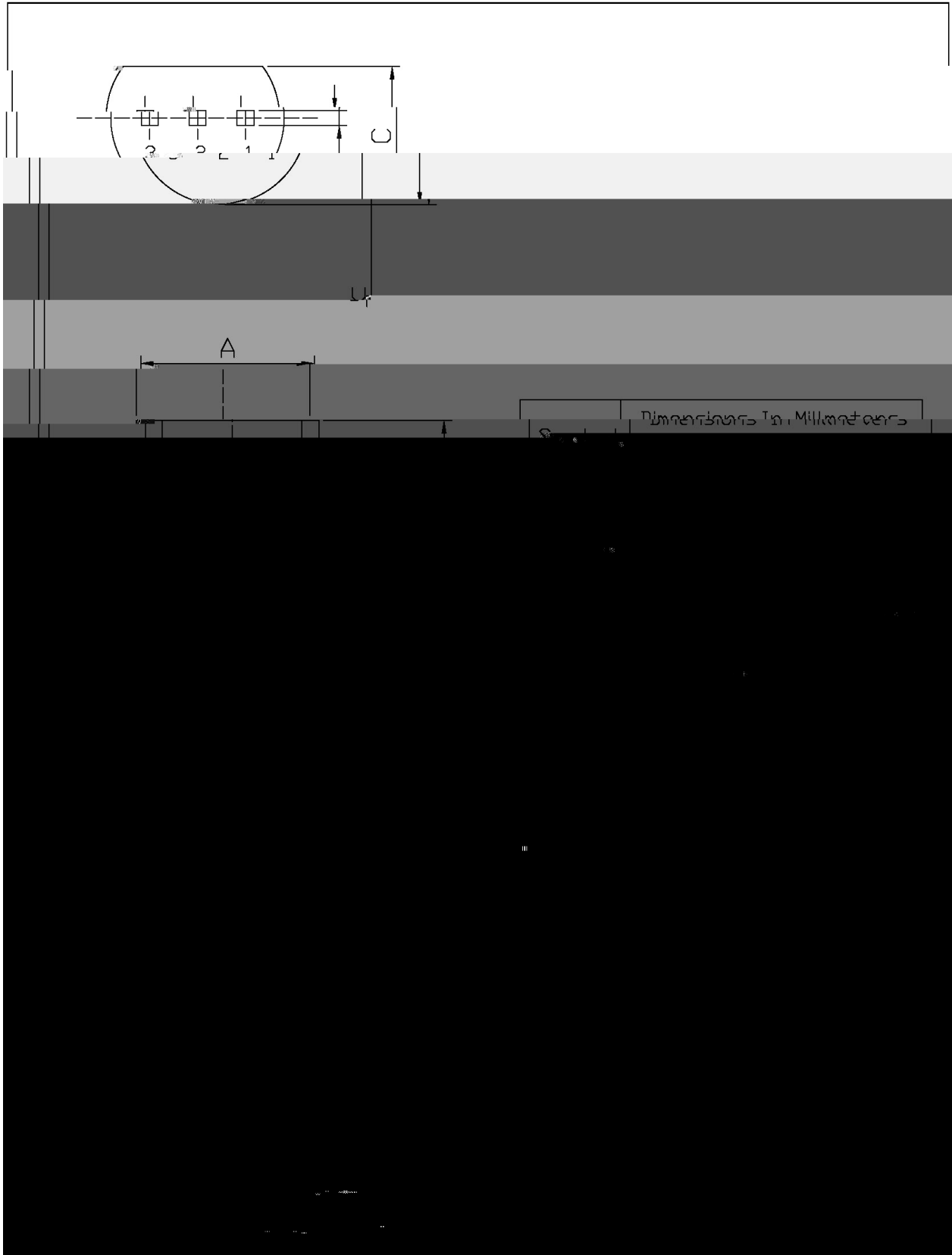
h_{FE} Classifications Symbol	R	O	Y	G
h_{FE} Range	40~80	70~140	120~240	200~400

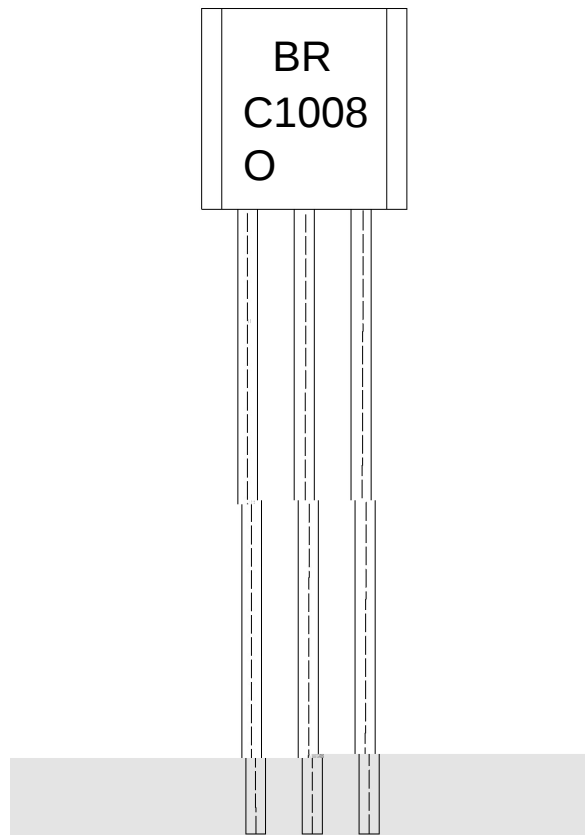
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	8.0	V
Collector Current - Continuous	I_C	700	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	8.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=2.0V$ $I_C=50mA$	40		400	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$		0.2	0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA$ $I_B=50mA$		0.86	1.1	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$	30	50		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		8.0		pF

T0-92

Unit: mm





BR:

C1008

O: h_{FE}

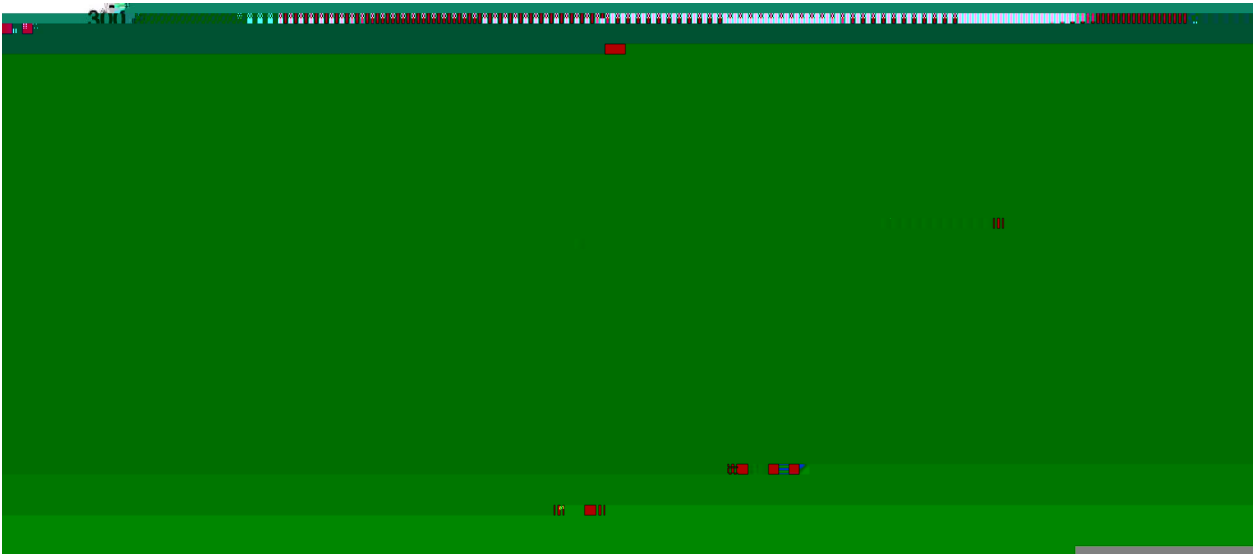
Note:

BR: Company Code.

C1008: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10 /sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type	Units	Dimension 314	0
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